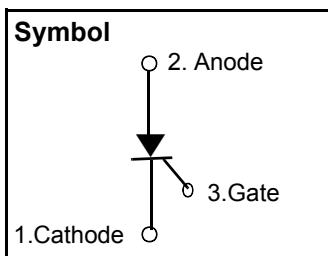
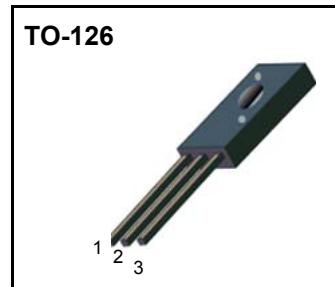


Sensitive Gate Silicon Controlled Rectifiers



BV_{DRM} = 600V
I_{T(RMS)} = 5A
I_{TSM} = 36A



Features

- ◆ Repetitive Peak Off-State Voltage : 600V
- ◆ R.M.S On-State Current (I_{T(RMS)}= 5 A)
- Non-isolated TO-126 Package

General Description

Apollo Electron's SCR is suitable for the application where requiring high bidirectional blocking voltage capability and also suitable for over voltage protection, motor control circuit in power tool, inrush current limit circuit and heating control system.

Absolute Maximum Ratings (T_J = 25°C unless otherwise specified)

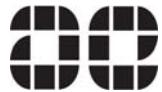
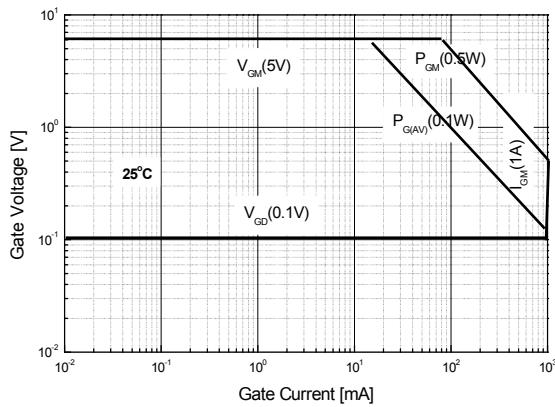
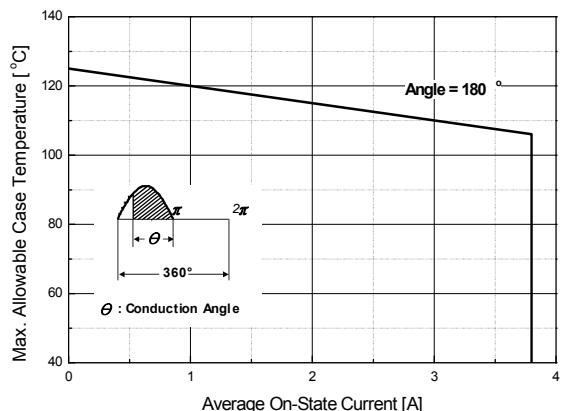
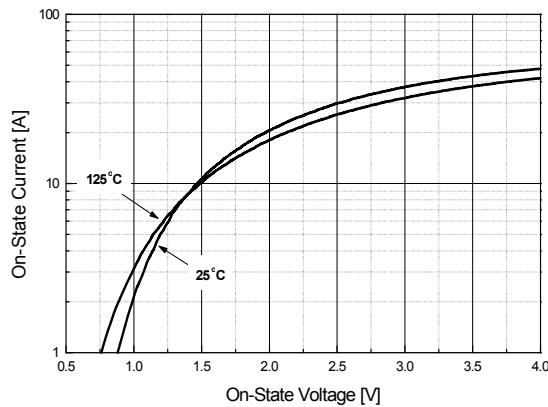
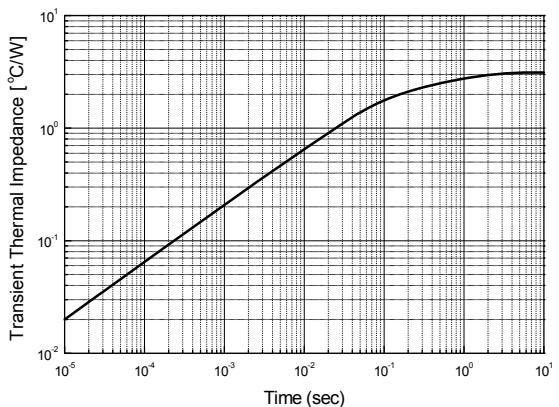
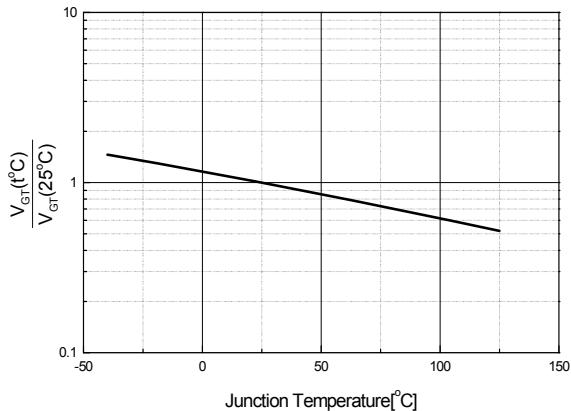
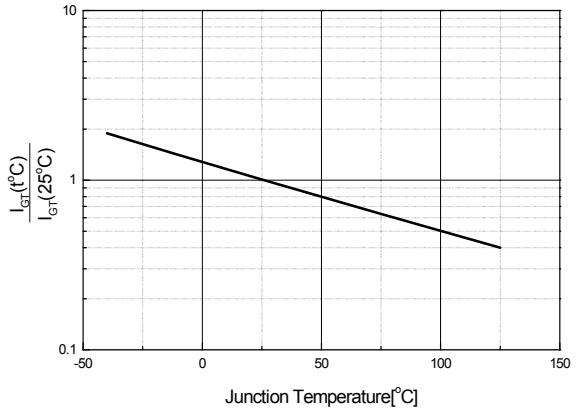
Symbol	Parameter	Condition	Ratings	Units
V _{DRM}	Repetitive Peak Off-State Voltage	sine wave,50 to 60Hz	600	V
I _{T(RMS)}	R.M.S On-State Current	180° Conduction Angle	5	A
I _{TSM}	Surge On-State Current	1/2 Cycle, 60Hz, Sine Wave Non-Repetitive	36	A
P _{GM}	Forward Peak Gate Power Dissipation	T _j = 110 °C	1	W
P _{G(AV)}	Forward Average Gate Power Dissipation	T _j = 110 °C	0.1	W
I _{FGM}	Forward Peak Gate Current	T _j = 110 °C	1	A
T _J	Operating Junction Temperature		- 40 ~ 125	°C
T _{TSG}	Storage Temperature		- 40 ~ 150	°C

CR6C60S



Electrical Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Items	Conditions	Ratings			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive Peak Off-State Current	$V_{AK} = V_{DRM}$ $T_j = 125^\circ\text{C}$	—	—	100	uA
V_{TM}	Peak On-State Voltage (1)	$I_T = 10\text{A}$	—	—	1.7	V
I_{GT}	Gate Trigger Current (2)	$V_{AK} = 12\text{V(DC)}$, $R_L = 100 \Omega$	—	—	200	uA
V_{GT}	Gate Trigger Voltage (2)	$V_D = 12\text{V(DC)}$, $R_L = 100 \Omega$	—	—	1.2	V
V_{GD}	Non-Trigger Gate Voltage (1)	$V_{AK} = 12\text{V}$, $R_L = 100 \Omega$ $T_j = 125^\circ\text{C}$	0.1	—	—	V
dv/dt	Critical Rate of Rise Off-State Voltage	Linear slope upto $DV = V_{DRM} 67\%$, Gate open $T_j = 125^\circ\text{C}$	10	—	—	V/us
I_H	Holding Current	$V_D = 24\text{V}$, $I_{GT} = 50\text{mA}$	—	—	5	mA

**CR6C60S****Fig 1. Gate Characteristics****Fig 2. Maximum Case Temperature****Fig 3. Typical Forward Voltage****Fig 4. Thermal Response****Fig 5. Typical Gate Trigger Voltage vs. Junction Temperature****Fig 6. Typical Gate Trigger Current vs. Junction Temperature**



CR6C60S

Fig 7. Typical Holding Current

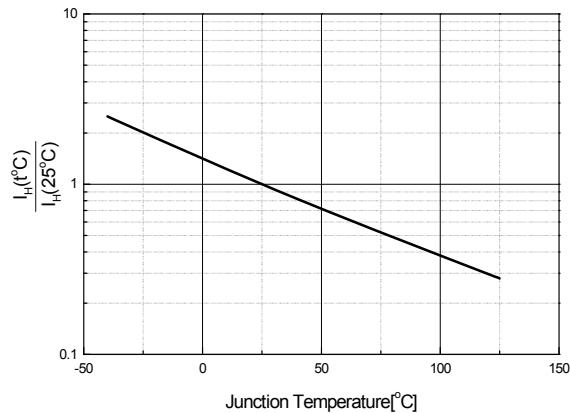
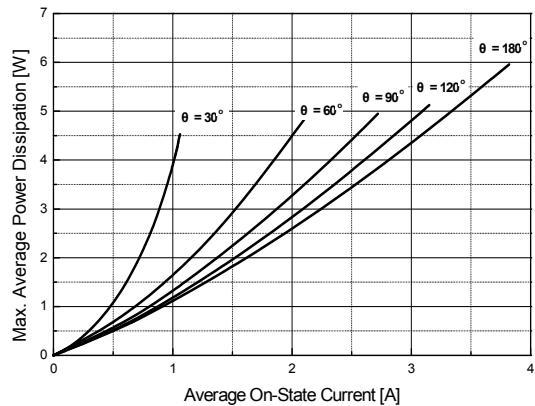


Fig 8. Power Dissipation



**CR6C60S****TO-126 Package Dimension**

Symbol	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.417	2.547	2.677	0.095	0.1	0.105
A1	1.14	1.32	1.5	0.045	0.052	0.059
b	0.71	0.76	0.81	0.028	0.03	0.032
b1	1.22	1.27	1.32	0.048	0.05	0.052
c	0.45	0.525	0.6	0.018	0.021	0.024
D	7.479	7.6145	7.75	0.295	0.3	0.305
E	10.875	10.925	10.975	0.428	0.43	0.432
e		2.285			0.09	
e1	4.5	4.56	4.62	0.178	0.18	0.182
L	15.25	15.5	15.75	0.6	0.61	0.62
L1	2.1	2.2	2.3	0.083	0.087	0.091
P	3.835	3.885	3.935	0.151	0.153	0.155
F	2.92	3.05	3.18	0.115	0.12	0.125

